Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2575	(antifuse or antifusing or antifusible or anti-fuse or anti-fusing or anti-fusible) same (drain or gate or mos or mosfet or transistor or fet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 08:39
L2	15	(antifuse or antifusing or antifusible or anti-fuse or anti-fusing or anti-fusible) same (drain or gate or mos or mosfet or transistor or fet) same (Idd or (source or drain) near2 extension)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 08:53
L7	131	(antifuse or antifusing or antifusible or anti-fuse or anti-fusing or anti-fusible) near10 (gate near2 (dielectric or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 09:58
L9	392	(antifuse or antifusing or antifusible or anti-fuse or anti-fusing or anti-fusible) and (source) near2 (drain) near2 (overlap or overlapping or overlapped or joining or joined or connected or connecting or connection)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 10:18
L10	68	(antifuse or antifusing or antifusible or anti-fuse or anti-fusing or anti-fusible) and (channel) near2 (ldd or doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 10:24
L11	32	(antifuse or antifusing or antifusible or anti-fuse or anti-fusing or anti-fusible) and (source or drain) near2 (path or conduit or short or shorting or shorted or interconnect or connection) near2 (channel or well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 10:35
L12	59	(antifuse or antifusing or antifusible or anti-fuse or anti-fusing or anti-fusible) and (channel) near2 (narrow or small)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 10:42
L14	1266	(mos or mosfet or fet or nmos or pmos or cmos or misfet or mesfet) and ((source) near2 (overlapping or overlapped or overlap or touching) near2 drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 10:48
L15	611	(mos or mosfet or fet or nmos or pmos or cmos or misfet or mesfet) and ((source) near (overlapping or overlapped or overlap or touching) near drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 10:49
L16	12	(mos or mosfet or fet or nmos or pmos or cmos or misfet or mesfet) and ((source) near (overlapping or overlapped or overlap or touching) near drain) near10 ldd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/11 10:49